

## **In th Claims**

Claims 1-36 (cancelled).

Claim 37 (original): A method of forming a capacitor, comprising:

forming a layer comprising titanium and nitrogen over a substrate, the layer comprising titanium and nitrogen being at least a portion of a first capacitor electrode;

forming a layer comprising aluminum oxide over the layer comprising titanium and nitrogen;

forming a high-k dielectric material over the layer comprising aluminum oxide, the high-k dielectric material comprising a composition other than aluminum oxide; and

forming a second capacitor electrode over the high-k dielectric material.

Claim 38 (original): The method of claim 37 wherein the substrate comprises a conductive material; wherein the layer comprising titanium and nitrogen is formed to be physically against the conductive material; and wherein the conductive material and the layer comprising titanium and nitrogen are together incorporated into the first capacitor electrode.

Claim 39 (original): The method of claim 38 wherein the conductive material is conductively-doped silicon.

Claim 40 (original): The method of claim 38 wherein the conductive material is conductively-doped rugged silicon.

Claim 41 (original): The method of claim 37 wherein the layer comprising aluminum oxide is formed by one or both of atomic layer deposition and chemical vapor deposition.

Claim 42 (original): The method of claim 37 wherein the high-k dielectric material is selected from the group consisting of  $\text{Ta}_2\text{O}_5$ ,  $\text{HfO}_x$ ,  $\text{ZrO}_y$ , barium titanate, barium strontium titanate, strontium titanate, and lead zirconate titanate, where x and y are numbers greater than 0.

Claim 43 (original): The method of claim 37 wherein the layer comprising aluminum oxide is a first layer comprising aluminum oxide, and further comprising forming a second layer comprising aluminum oxide over the high-k dielectric material.

Claim 44 (original): The method of claim 43 wherein the layer comprising titanium and nitrogen is a first layer comprising titanium and nitrogen, and further comprising forming a second layer comprising titanium and nitrogen over the second layer comprising aluminum oxide.

Claim 45 (original): The method of claim 44 wherein the first and second layers comprising titanium and nitrogen both consist essentially of titanium nitride.

Claim 46 (original): The method of claim 44 wherein the first and second layers comprising titanium and nitrogen both consist essentially of boron-doped titanium nitride.